

A STUDY OF THE OPERATING PARAMETERS OF CHAOTIC SEMICONDUCTOR LASERS

Thesis

Submitted to

The National Institute of Laser Enhanced Sciences
(NILES) - Cairo University

In Partial Fulfillment of the Requirements

For the Degree

of

Master of Science

In

Engineering Applications of Lasers

By

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2010

Approval Sheet

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Acknowledgement

All gratitude is due to Allah. Thence I would like to thank all those who helped and supported me till the eventual realization of this thesis.

I would like to thank my advisor Prof Dr. Mohy Saad, Dr. Jala El-Azab and Dr. Ashraf El-Meligy for their time, their guidance, invaluable suggestions and continuous encouragement since the initiation of this work till the final touches. I also want to thank them for providing me with useful package that helped me in the survey in the relevant literature. It was a great honor to work under their guidance and supervision.

Special thanks are due to Prof Dr. Adel El-Nadi for his great assistance and encouragement and for Prof Dr. Amen Fahem for his great encouragement. Also I would like to thank Dr. Alaa Hafez for his advice and encouragement. I would like also to thank my friends especially Eng. Mostafa El-Shershaby, Eng. Moamen Mahmoud, and Mr. Ahmed Fawzy who encouraged me and provided great moral support and sincere advice during my work in this thesis.

I also offer my warmest thanks to my wife and my children for their support and understanding of my duty to complete this work. Finally, deep thanks are to my mother with respect and love.

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